

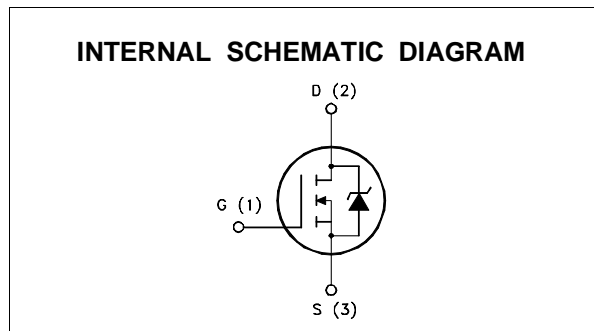
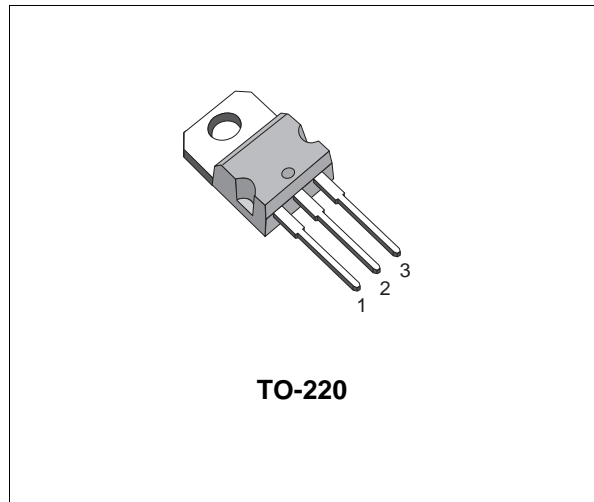
## N - CHANNEL ENHANCEMENT MODE POWER MOS TRANSISTOR

| TYPE    | V <sub>DSS</sub> | R <sub>DS(on)</sub> | I <sub>D</sub> |
|---------|------------------|---------------------|----------------|
| MTP6N60 | 600 V            | < 1.2 Ω             | 6.8 A          |

- TYPICAL R<sub>DS(on)</sub> = 1 Ω
- AVALANCHE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- APPLICATION ORIENTED CHARACTERIZATION

### APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- CHOPPER REGULATORS, CONVERTERS, MOTOR CONTROL, LIGHTING FOR INDUSTRIAL AND CONSUMER ENVIRONMENT



### ABSOLUTE MAXIMUM RATINGS

| Symbol              | Parameter   | Value      | Unit |
|---------------------|---|------------|------|
| V <sub>DS</sub>     | Drain-source Voltage (V <sub>GS</sub> = 0)            | 600        | V    |
| V <sub>DGR</sub>    | Drain- gate Voltage (R <sub>GS</sub> = 20 kΩ)         | 600        | V    |
| V <sub>GS</sub>     | Gate-source Voltage                                   | ± 20       | V    |
| I <sub>D</sub>      | Drain Current (continuous) at T <sub>c</sub> = 25 °C  | 6.8        | A    |
| I <sub>D</sub>      | Drain Current (continuous) at T <sub>c</sub> = 100 °C | 4.2        | A    |
| I <sub>DM</sub> (•) | Drain Current (pulsed)                                | 30         | A    |
| P <sub>tot</sub>    | Total Dissipation at T <sub>c</sub> = 25 °C           | 125        | W    |
|                     | Derating Factor                                       | 1          | W/°C |
| T <sub>stg</sub>    | Storage Temperature                                   | -65 to 150 | °C   |
| T <sub>j</sub>      | Max. Operating Junction Temperature                   | 150        | °C   |

(•) Pulse width limited by safe operating area

**THERMAL DATA**

|                       |  |     |      |      |
|-----------------------|--|-----|------|------|
| R <sub>thj-case</sub> | Thermal Resistance Junction-case               | Max | 1    | °C/W |
| R <sub>thj-amb</sub>  | Thermal Resistance Junction-ambient            | Max | 62.5 | °C/W |
| R <sub>thj-amb</sub>  | Thermal Resistance Case-sink                   | Typ | 0.5  | °C/W |
| T <sub>l</sub>        | Maximum Lead Temperature For Soldering Purpose |     | 300  | °C   |

**AVALANCHE CHARACTERISTICS**

| Symbol          | Parameter  | Max Value | Unit |
|-----------------|--|-----------|------|
| I <sub>AR</sub> | Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max, δ < 1%)                          | 6.8       | A    |
| E <sub>AS</sub> | Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 25 V)   | 460       | mJ   |
| E <sub>AR</sub> | Repetitive Avalanche Energy (pulse width limited by T <sub>j</sub> max, δ < 1%)  | 21        | mJ   |
| I <sub>AR</sub> | Avalanche Current, Repetitive or Not-Repetitive (T <sub>c</sub> = 100 °C, pulse width limited by T <sub>j</sub> max, δ < 1%) | 4.2       | A    |

**ELECTRICAL CHARACTERISTICS** (T<sub>case</sub> = 25 °C unless otherwise specified)

OFF

| Symbol               | Parameter   | Test Conditions  | Min. | Typ. | Max.      | Unit     |
|----------------------|---|--|------|------|-----------|----------|
| V <sub>(BR)DSS</sub> | Drain-source Breakdown Voltage                        | I <sub>D</sub> = 250 μA V <sub>GS</sub> = 0  | 600  |      |           | V        |
| I <sub>DSS</sub>     | Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0) | V <sub>DS</sub> = Max Rating<br>V <sub>DS</sub> = Max Rating x 0.8 T <sub>c</sub> = 125 °C |      |      | 25<br>250 | μA<br>μA |
| I <sub>GSS</sub>     | Gate-body Leakage Current (V <sub>DS</sub> = 0)       | V <sub>GS</sub> = ± 20 V   |      |      | ± 100     | nA       |

ON (\*)

| Symbol              | Parameter                         | Test Conditions   | Min. | Typ. | Max. | Unit |
|---------------------|-----------------------------------|---|------|------|------|------|
| V <sub>GS(th)</sub> | Gate Threshold Voltage            | V <sub>DS</sub> = V <sub>GS</sub> I <sub>D</sub> = 1 mA                                 | 2    | 3.1  | 4.5  | V    |
| R <sub>DS(on)</sub> | Static Drain-source On Resistance | V <sub>GS</sub> = 10V I <sub>D</sub> = 3 A  |      | 1    | 1.2  | Ω    |
| I <sub>D(on)</sub>  | On State Drain Current            | V <sub>DS</sub> > I <sub>D(on)</sub> x R <sub>DS(on)max</sub><br>V <sub>GS</sub> = 10 V | 6.8  |      |      | A    |

**DYNAMIC**

| Symbol              | Parameter                    | Test Conditions  | Min. | Typ. | Max. | Unit |
|---------------------|------------------------------|--|------|------|------|------|
| g <sub>fs</sub> (*) | Forward Transconductance     | V <sub>DS</sub> > I <sub>D(on)</sub> x R <sub>DS(on)max</sub> I <sub>D</sub> = 3 A | 2    | 4.8  |      | S    |
| C <sub>iss</sub>    | Input Capacitance            | V <sub>DS</sub> = 25 V f = 1 MHz V <sub>GS</sub> = 0                               |      | 1150 | 1500 | pF   |
| C <sub>oss</sub>    | Output Capacitance           |  |      | 160  | 240  | pF   |
| C <sub>rss</sub>    | Reverse Transfer Capacitance |  |      | 75   | 110  | pF   |

**ELECTRICAL CHARACTERISTICS** (continued)

**SWITCHING ON**

| Symbol                        | Parameter  | Test Conditions   | Min. | Typ.          | Max.      | Unit             |
|-------------------------------|--|---|------|---------------|-----------|------------------|
| $t_{d(on)}$<br>$t_r$          | Turn-on Time<br>Rise Time                                    | $V_{DD} = 300\text{ V}$ $I_D = 3\text{ A}$<br>$R_G = 50\ \Omega$ $V_{GS} = 10\text{ V}$<br>(see test circuit, figure 3) |      | 50<br>140     | 65<br>175 | ns<br>ns         |
| $(di/dt)_{on}$                | Turn-on Current Slope  | $V_{DD} = 480\text{ V}$ $I_D = 6\text{ A}$<br>$R_G = 50\ \Omega$ $V_{GS} = 10\text{ V}$<br>(see test circuit, figure 5) |      | 240           |           | A/ $\mu\text{s}$ |
| $Q_g$<br>$Q_{gs}$<br>$Q_{gd}$ | Total Gate Charge<br>Gate-Source Charge<br>Gate-Drain Charge | $V_{DD} = 480\text{ V}$ $I_D = 6\text{ A}$ $V_{GS} = 10\text{ V}$   |      | 78<br>8<br>41 | 98        | nC<br>nC<br>nC   |

**SWITCHING OFF**

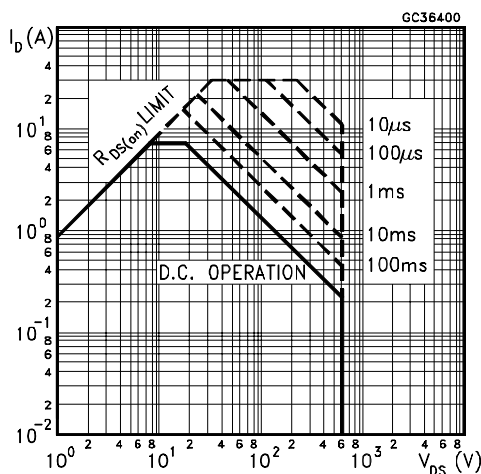
| Symbol                          | Parameter   | Test Conditions   | Min. | Typ.             | Max.             | Unit           |
|---------------------------------|---|---|------|------------------|------------------|----------------|
| $t_{r(Voff)}$<br>$t_f$<br>$t_c$ | Off-voltage Rise Time<br>Fall Time<br>Cross-over Time | $V_{DD} = 480\text{ V}$ $I_D = 6\text{ A}$<br>$R_G = 50\ \Omega$ $V_{GS} = 10\text{ V}$<br>(see test circuit, figure 5) |      | 100<br>27<br>145 | 125<br>34<br>180 | ns<br>ns<br>ns |

**SOURCE DRAIN DIODE**

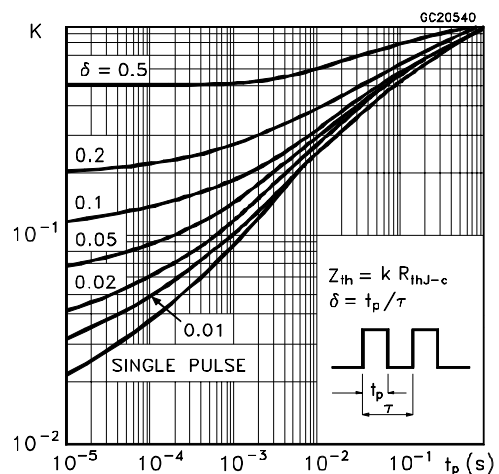
| Symbol                            | Parameter  | Test Conditions   | Min. | Typ.              | Max.      | Unit                     |
|-----------------------------------|--|---|------|-------------------|-----------|--------------------------|
| $I_{SD}$<br>$I_{SDM}(\bullet)$    | Source-drain Current<br>Source-drain Current (pulsed)                        |   |      |                   | 3.8<br>24 | A<br>A                   |
| $V_{SD} (*)$                      | Forward On Voltage   | $I_{SD} = 6\text{ A}$ $V_{GS} = 0$  |      |                   | 2         | V                        |
| $t_{rr}$<br>$Q_{rr}$<br>$I_{RRM}$ | Reverse Recovery Time<br>Reverse Recovery Charge<br>Reverse Recovery Current | $I_{SD} = 6\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$<br>$V_{DD} = 100\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$<br>(see test circuit, figure 5) |      | 750<br>13.5<br>38 |           | ns<br>$\mu\text{C}$<br>A |

(\*) Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %  
 (•) Pulse width limited by safe operating area

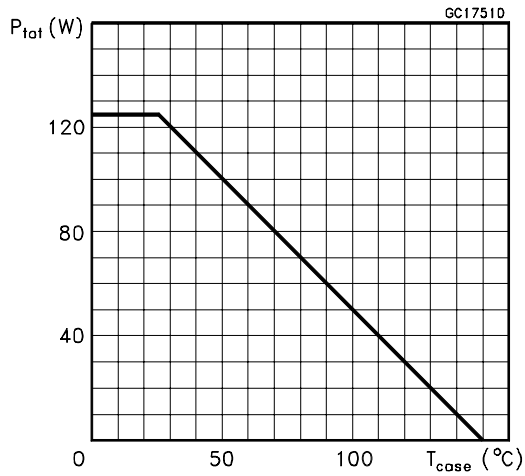
**Safe Operating Area**



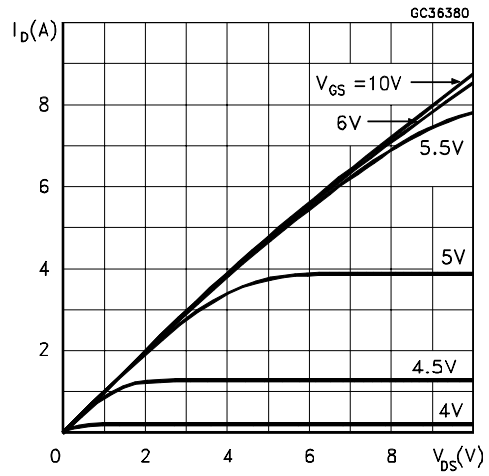
**Thermal Impedance**



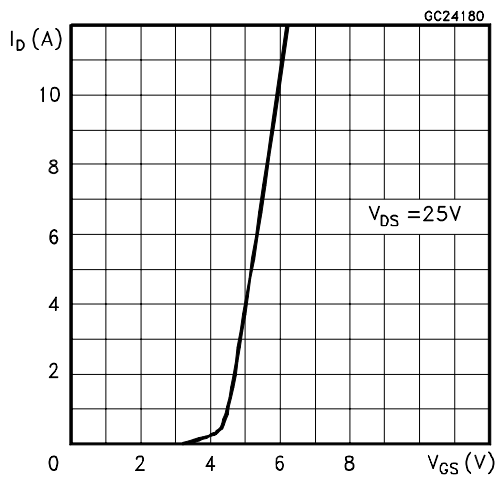
Derating Curve



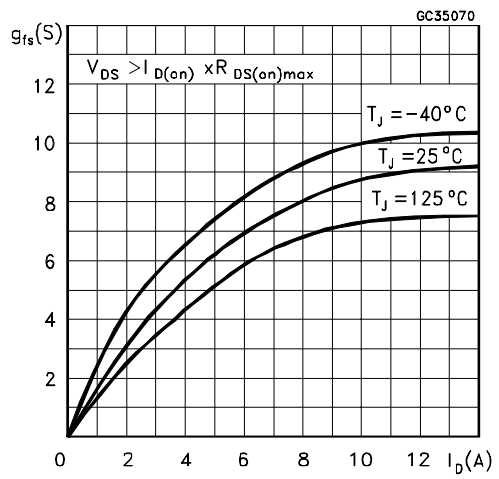
Output Characteristics



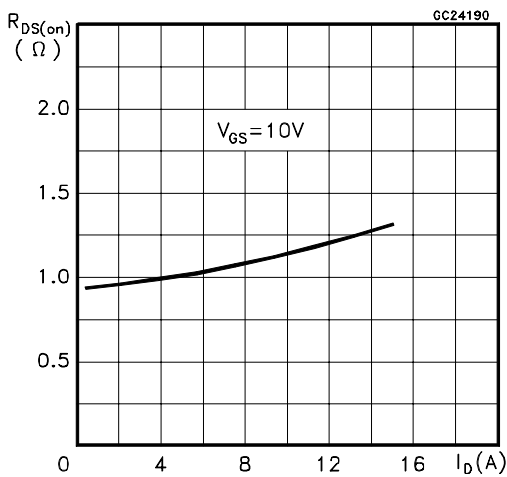
Transfer Characteristics



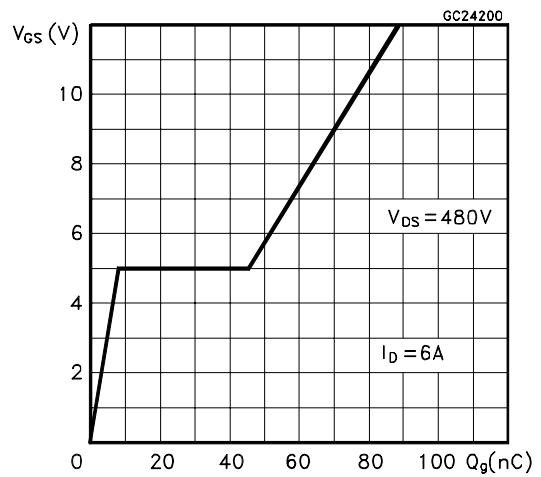
Transconductance



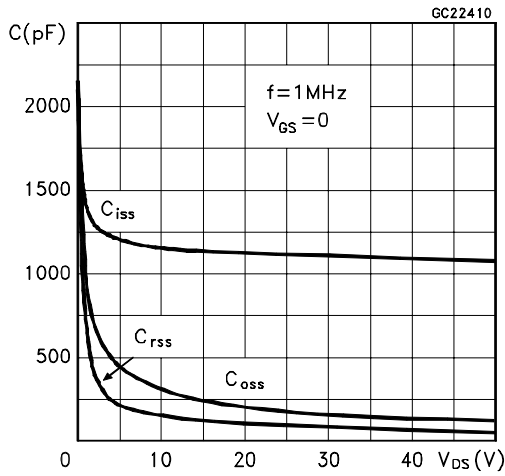
Static Drain-source On Resistance



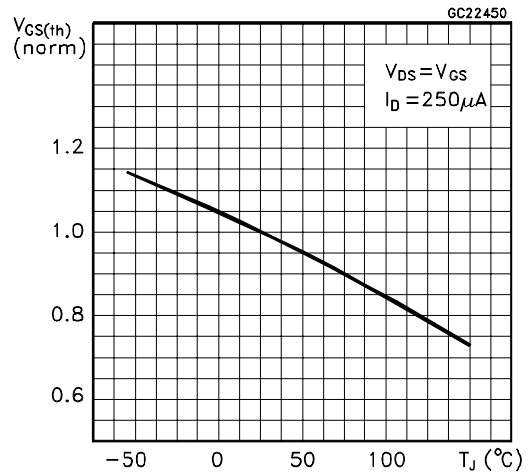
Gate Charge vs Gate-source Voltage



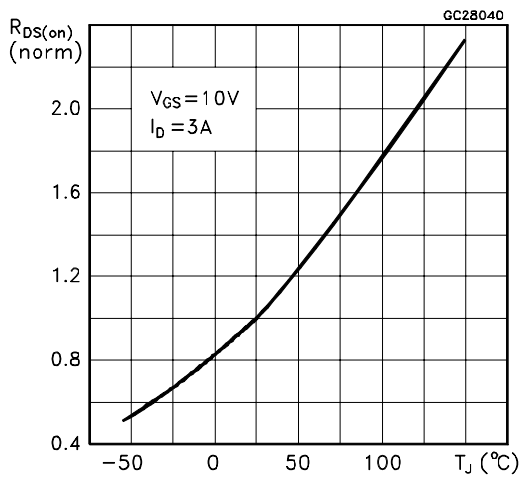
Capacitance Variations



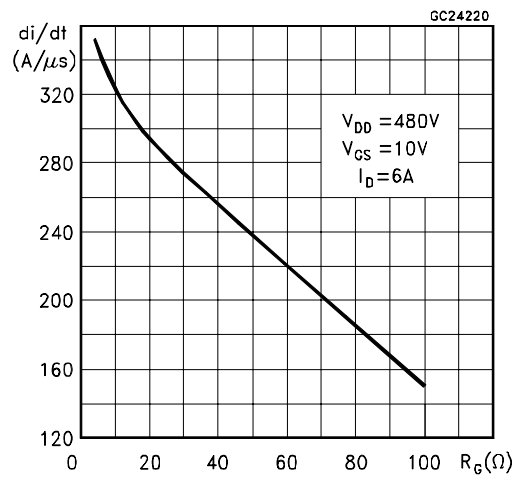
Normalized Gate Threshold Voltage vs Temperature



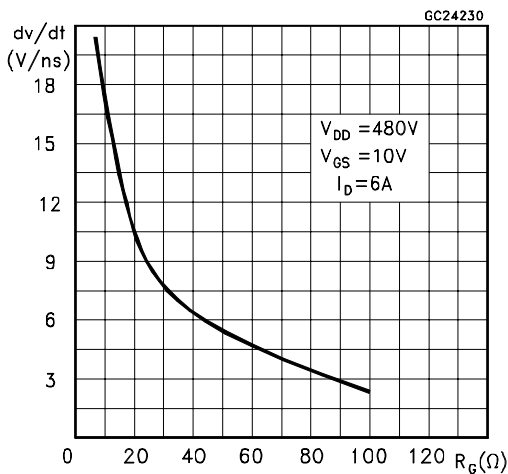
Normalized On Resistance vs Temperature



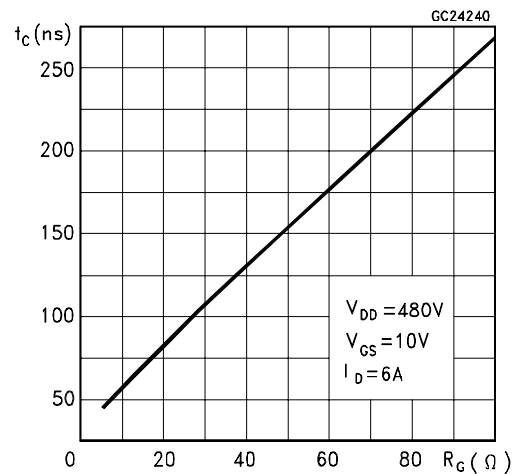
Turn-on Current Slope



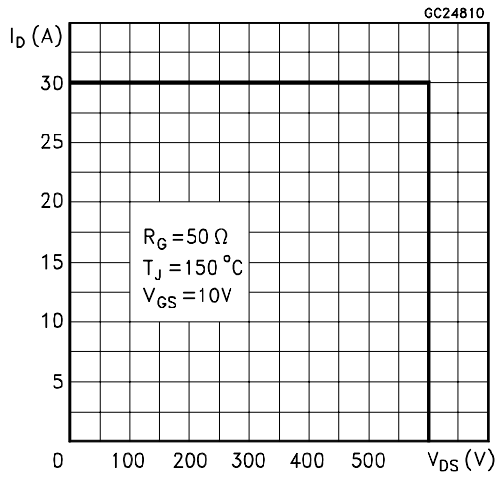
Turn-off Drain-source Voltage Slope



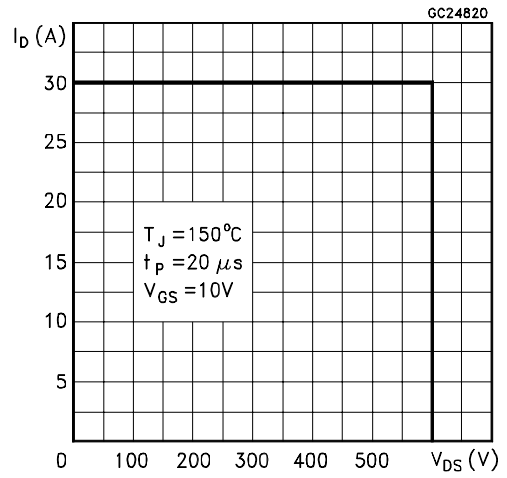
Cross-over Time



Switching Safe Operating Area



Accidental Overload Area



Source-drain Diode Forward Characteristics

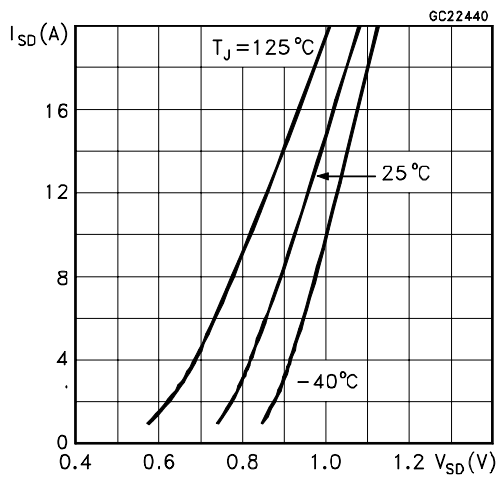


Fig. 1: Unclamped Inductive Load Test Circuits

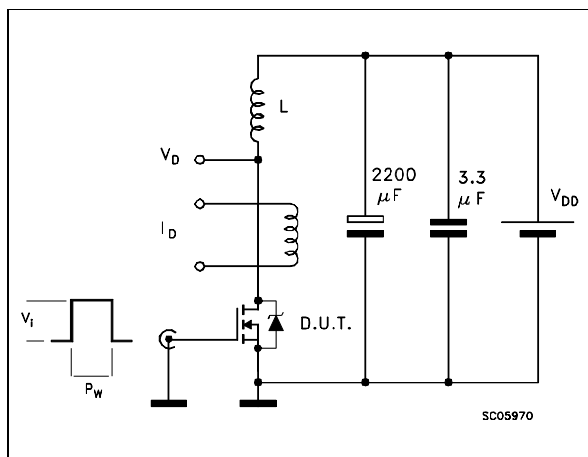
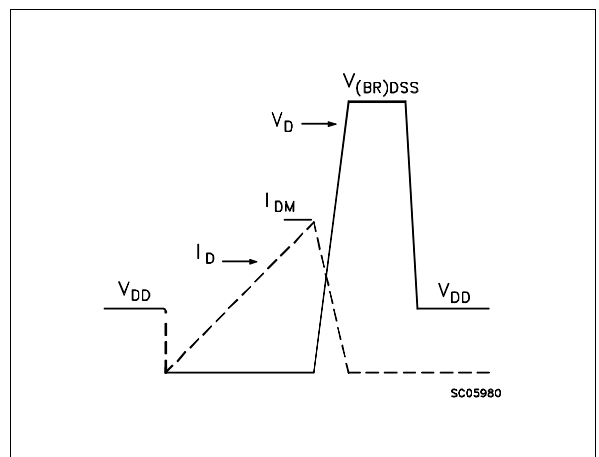
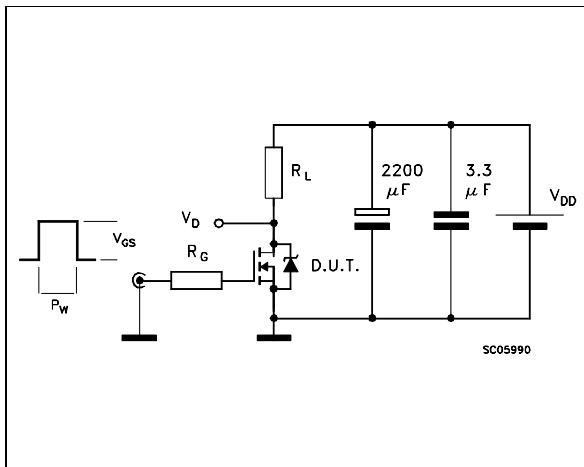


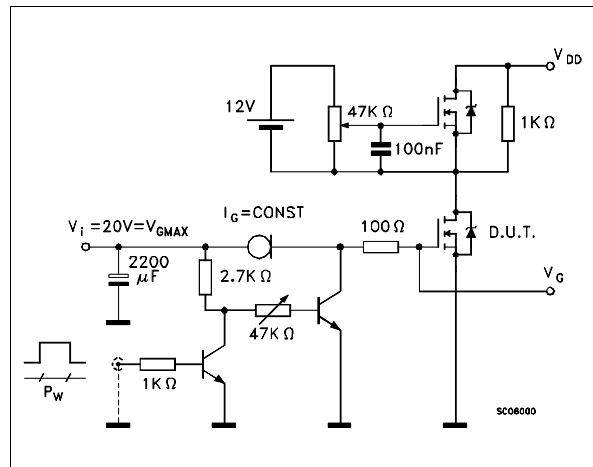
Fig. 2: Unclamped Inductive Waveforms



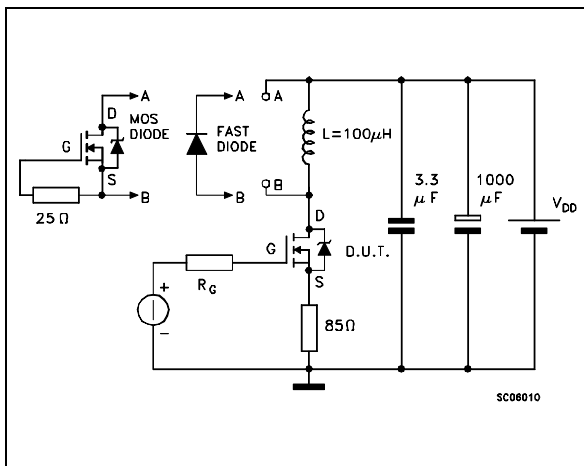
**Fig. 3: Switching Times Test Circuits For Resistive Load**



**Fig. 4: Gate Charge Test Circuit**

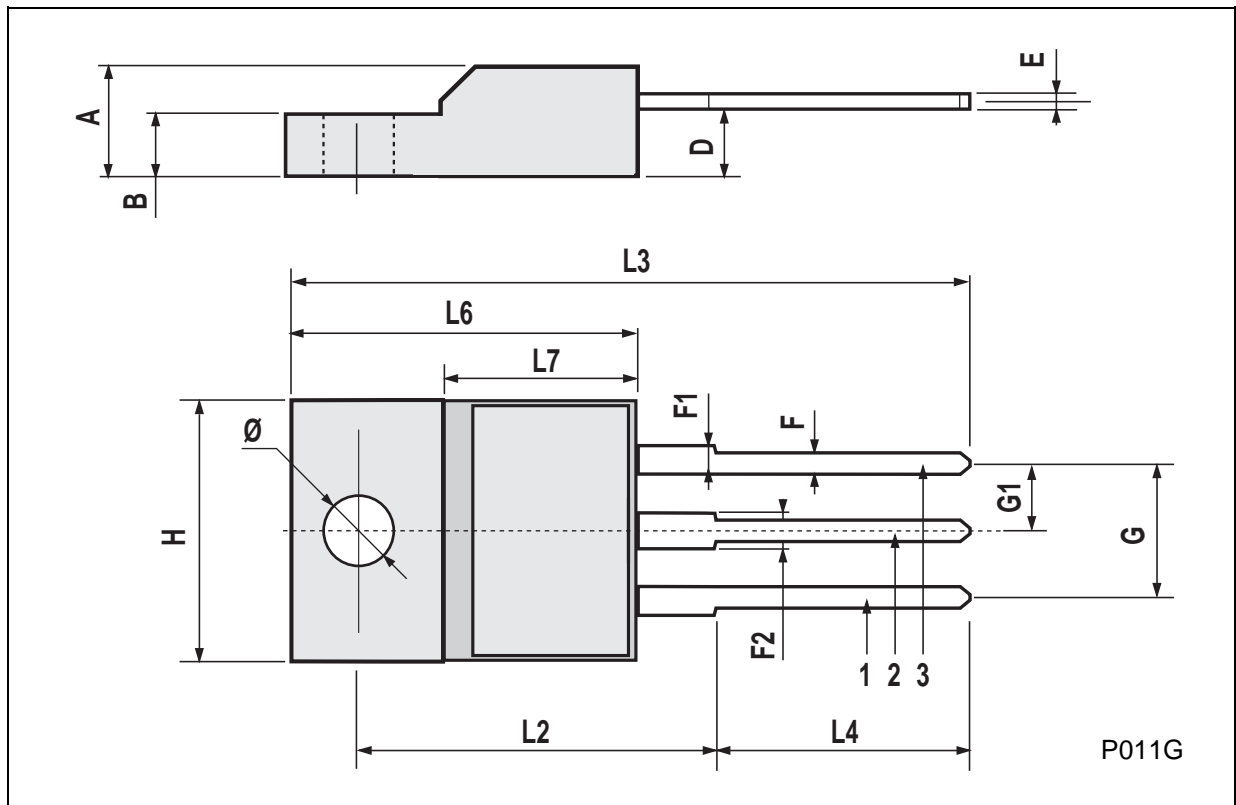


**Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times**



**ISOWATT220 MECHANICAL DATA**

| DIM. | mm   |      |      | inch  |       |       |
|------|------|------|------|-------|-------|-------|
|      | MIN. | TYP. | MAX. | MIN.  | TYP.  | MAX.  |
| A    | 4.4  |      | 4.6  | 0.173 |       | 0.181 |
| B    | 2.5  |      | 2.7  | 0.098 |       | 0.106 |
| D    | 2.5  |      | 2.75 | 0.098 |       | 0.108 |
| E    | 0.4  |      | 0.7  | 0.015 |       | 0.027 |
| F    | 0.75 |      | 1    | 0.030 |       | 0.039 |
| F1   | 1.15 |      | 1.7  | 0.045 |       | 0.067 |
| F2   | 1.15 |      | 1.7  | 0.045 |       | 0.067 |
| G    | 4.95 |      | 5.2  | 0.195 |       | 0.204 |
| G1   | 2.4  |      | 2.7  | 0.094 |       | 0.106 |
| H    | 10   |      | 10.4 | 0.393 |       | 0.409 |
| L2   |      | 16   |      |       | 0.630 |       |
| L3   | 28.6 |      | 30.6 | 1.126 |       | 1.204 |
| L4   | 9.8  |      | 10.6 | 0.385 |       | 0.417 |
| L6   | 15.9 |      | 16.4 | 0.626 |       | 0.645 |
| L7   | 9    |      | 9.3  | 0.354 |       | 0.366 |
| ∅    | 3    |      | 3.2  | 0.118 |       | 0.126 |





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